Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-60. (Cancelled)

61. (New) A method for manufacturing a coated circular substrate, comprising

(a) providing a circular area with a radius in a sputtering chamber

(b) introducing into said sputtering chamber one substrate of said radius or more than one substrate defining in combination an area of said radius;

(c) rotating said at least one substrate about a first central axis of said circular area;

(d) providing a single magnetron sputtering source with a circular sputtering surface and having a second central axis oblique with respect to and intersecting said first central axis;

(e) selecting the diameter of said circular area to be larger than the diameter of said circular sputtering surface;

(f) selecting an intersection angle of said first and second central axis to be:

$$43° \leq \beta \geq 50°; \text{ and}$$

(g) magnetron sputter coating said at least one substrate by said single magnetron sputtering source.

62. (New) The method of claim 61, further comprising selecting said intersection angle β to be approximately 45°.

63. (New) The method of claim 61, further comprising generating with said single magnetron sputtering source at least one circular erosion ditch in said sputtering surface, said erosion ditch having a circular locus r_{Tr} wherein said second central axis intersects said at least one substrate at a distance D from said sputter surface, and selecting r_{Tr} to be

$$1/4 \leq r_{Tr} / D \leq 2/3.$$

64. (New) The method of claim 61, wherein said circular sputtering surface has a diameter Φ_T and said second central axis intersects said at least one substrate at a distance D from said sputtering surface, further comprising selecting Φ_T to be:

$$3/4 \leq \Phi_T / D \leq 2.$$

65. (New) The method of claim 61, further comprising selecting Φ_T to be ≈ 1.2 D.

66. (New) The method of claim 61, wherein said circular area has a diameter Φ_S, and said second central axis intersects said at least one substrate at a distance D from said sputtering surface, further comprising selecting Φ_S to be:

$$\Phi_\$ /4\ D \leq 1.8.$$

67. (New) The method of claim 61, wherein said circular area has a diameter Φ_S, and said circular sputtering surface has a diameter Φ_T, further comprising selecting Φ_T to be:

$$1 \leq \Phi_S / \Phi_T \leq 2.4.$$

68. (New) The method of claim 61, wherein said circular area has a diameter of Φ_S selected to be:

$$50\ mm \leq \Phi_S \leq 400\ mm.$$

69. (New) The method of claim 68, wherein Φ_S is selected to be:

$$50\ mm \leq \Phi_S \leq 300\ mm.$$

70. (New) The method of of claim 61, wherein said at least one substrate is one of a data storage disc and of a wafer.

71. (New) The method of claim 61, wherein said at least one substrate has a diameter of one of 64 mm, 120 mm, 160 mm, 240 mm.